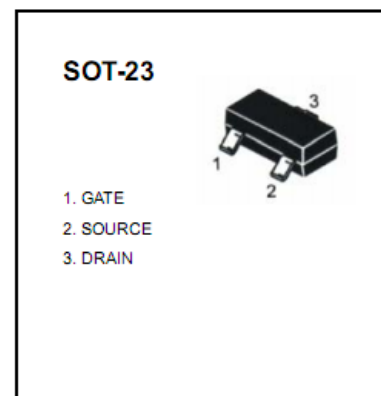
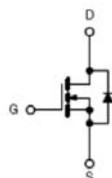


SOT-23 Plastic-Encapsulate Transistors

FEATURES

Trench FET Power MOSFET

MARKING: A2SHB



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source voltage	20	V
V_{GS}	Gate-Source voltage	± 10	V
I_D	Drain current	3.5	A
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	20			V
Gate-Threshold Voltage	$V_{th(GS)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.7	1.1	V
Gate-body Leakage	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 10V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	μA
Drain-Source On-Resistance	$r_{DS(ON)}$	$V_{GS}=2.5V, I_D=2A$		47	100	m Ω
		$V_{GS}=4.5V, I_D=3A$		36	55	m Ω

Package Outline Dimensions (UNIT: mm)

SOT-23

